

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-22 (Canceled).

23. (Currently Amended) A semiconductor device having a ferroelectric capacitor comprising:

a lower electrode laminated on one side to a substrate;

a ferroelectric thin film constructed of at least three layers including a lowermost layer, an uppermost layer and an intermediate layer located between the lowermost layer and the uppermost layer, said lowermost layer only being directly laminated on another side of said lower electrode; and

an upper electrode only being directly laminated, on one side, to said uppermost layer, so that said intermediate layer does not directly contact either said lower electrode or said upper electrode,

wherein a crystal grain of ~~at least one of the lowermost layer and the uppermost~~ layer is smaller than a crystal grain of the intermediate layer.

24. (Original) A semiconductor device as claimed in claim 23, wherein
a crystal grain of the lowermost layer and a crystal grain of the uppermost layer is smaller than a crystal grain of the intermediate layer.

Claims 25-27 (Canceled).

28. (Currently Amended) A semiconductor device having a ferroelectric capacitor comprising:

a lower electrode laminated on one side to a substrate;

a ferroelectric thin film constructed of at least three layers including a lowermost layer, an uppermost layer and an intermediate layer located between the lowermost layer and the uppermost layer, said lowermost layer only being directly laminated on another side of said lower electrode; and

an upper electrode only being directly laminated, on one side, to said uppermost layer, so that said intermediate layer does not directly contact either said lower electrode or said upper electrode,

~~wherein~~ the lowermost layer being formed of uniform minute crystal grains having small pinhole size gaps therebetween and with a crystalline nucleus density of the lowermost layer being is higher than those of the intermediate and uppermost layers.

Claim 29 (Canceled).

30. (Currently Amended) A semiconductor device having a ferroelectric capacitor comprising:

a lower electrode laminated on one side to a substrate;

a ferroelectric thin film laminated ~~on the lower electrode and~~ constructed of five layers including a lowermost layer, an uppermost layer and three intermediate layers

located between the lowermost layer and the uppermost layer, said lowermost layer only being directly laminated on another side of said lower electrode; and

an upper electrode only being directed laminated, on one side, to said uppermost layer, so that none of said three intermediate layers directly contact either said lower electrode or said upper electrode, the ferroelectric thin film,

wherein a crystal grain of at least one of the lowermost layer and the uppermost layer is smaller than a crystal grain of the intermediate layers.

31. (Previously Presented) A semiconductor device as claimed in claim 30, wherein

a crystal grain of the lowermost layer and a crystal grain of the uppermost layer is smaller than a crystal grain of the intermediate layers.

32. (Currently Amended) A semiconductor device having a ferroelectric capacitor comprising:

a lower electrode laminated on one side to a substrate;

a ferroelectric thin film laminated ~~on the lower electrode,~~ constructed of five layers including a lowermost layer, an uppermost layer and three intermediate layers located between the lowermost layer and the uppermost layer, said lowermost layer only being directly laminated on another side of said lower electrode; and

an upper electrode only being directed laminated on one side, to said uppermost layer, so that none of said three intermediate layers directly contact either said lower electrode or said upper electrode,~~the ferroelectric thin film,~~

wherein a crystalline nucleus density of the lowermost layer is higher than those of the uppermost and intermediate layers.

Claims 33-36 (Canceled).